

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	43	lim near sang.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:05	
2	BRS	L2	1	1 and (ge-mn)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:04	
3	BRS	L3	73	song near sang.in.	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:05	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	1	3 and (ge-mn)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:05	
5	BRS	L5	11	(ge-mn)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:12	
6	BRS	L6	2	(ge-mn) near25 (amorphous)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	2	(ge-mn) near5 (magnetic)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:13	
8	BRS	L9	2	((mn) near (magnetic)) near25 (ge) near (semiconductor)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:08	
9	BRS	L8	80	(mn) near (magnetic)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	0	5 and thermo	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:12	
11	BRS	L11	2	5 and dynamic	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:12	
12	BRS	L12	4	(ge-mn) near5 (alloy)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:14	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	11	(ge-mn) and (alloy)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:14	
14	BRS	L14	2	(ge-mn) and (curie)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:15	
15	BRS	L15	1	(film near (ge-mn))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:16	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	5	(film near15 (ge-mn))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:16	
17	BRS	L17	5	(film near35 (ge-mn))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:16	
18	BRS	L18	10	(film and (ge-mn))	US-PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 29 15:16	

	U	1	PT	P	Document ID	Issue Date	Page s	Title
1					US 2004018230 7 A1	20040923	11	Method of fabricating Ge-Mn magnetic semi conductors with high cure temperature
2					US 2004010448 0 A1	20040603	7	Method of producing an ultra thin electrically conducting film with very low electrical resistance
3					US 4690714 A	19870901	16	Method of making active solid state devices

	U	1	PT	P	Document ID	Issue Date	Page s	Title
4					US 4371406 A	19830201	15	Solid-state device



	U	1	PT	P	Document ID	Issue Date	Page s	Title
5					US 4136435 A	19790130	16	Method for making solid-state device
6					US 4132571 A	19790102	9	Growth of polycrystalline semiconductor film with intermetallic nucleating layer

	U	1	PT	P	Document ID	Issue Date	Page s	Title
7	X				US 3765956 A	19731016	16	SOLID-STATE DEVICE
8	X				JP 04149812 A	19920522	ERR	MAGNETIC HEAD
9	X				JP 61210516 A	19860918	ERR	MAGNETIC RECORDING MEDIUM AND ITS PRODUCTION
10	X				DE 10354438 A	20040826	11	Production of magnetic germanium- manganese semiconductors of high Curie temperature useful in spin electronics structural component production